

# **DOPING-LESS BIPOLAR TRANSISTORS: DESIGN AND INVESTIGATION**

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# **DOPING-LESS BIPOLAR TRANSISTORS: DESIGN AND INVESTIGATION**

by

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*Submitted*

*in fulfilment of the requirements of the degree of*

**Doctor of Philosophy**

*to the*



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## CERTIFICATE

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This is to certify that the thesis entitled “*Doping-less Bipolar Transistor: Design and Investigation*” being submitted by **Mrs Kanika** for the award of the degree of **Doctor of Philosophy** in the Department of Electrical Engineering, **Indian Institute of Technology Delhi**, is a record of bonafied work done by her under my supervision and guidance. The matter embodied in this thesis has not been submitted for the award of any other degree or diploma.

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# ABSTRACT

Although CMOS is increasingly used in integrated circuits, the bipolar transistors are extensively used in high speed and mixed signal circuits. BJTs are still widely investigated to enhance their electrical performance and widen their applications. However, since its invention, bipolar transistors could not be made without doping the semiconductor multiple times to create the emitter, base and the collector region. Doping leads to the defect formation and thermal budgets are a major concern in modern semiconductor technology.

This research work is focussed on realizing bipolar transistors on an intrinsic semiconductor without the need for any doping. Absence of the doped regions avoids the necessity of complicated thermal budgets.

In this thesis, a novel doping-less bipolar transistor named Bipolar Charge Plasma Transistor (BCPT) is first proposed. Using metal electrodes of appropriate work functions, the emitter, base and the collector regions of the BJT are created by inducing electron and hole plasma into the undoped semiconductor. Using two-dimensional simulations, it is demonstrated that the BCPT exhibits a good transistor action with a significantly larger current gain compared to a conventional BJT with the same device geometry.

Since, Schottky collector BJTs provide a better trade-off between the base-collector capacitance and the collector transit time, we have also investigated a Schottky collector bipolar charge plasma transistor (SC-BCPT) on an undoped silicon-on-insulator (SOI) film by inducing charge plasma in the emitter and the base region of the transistor. This research work demonstrates that the proposed SC-BCPT exhibits a significantly higher current gain, higher cut-off frequency and a better current drive compared to that of its conventional counterpart.

To further improve the electrical characteristics of the BCPT, a doping-less Vertical Bipolar Charge Plasma Transistor (V-BCPT) with a buried metal layer on SOI is reported in

this thesis. Using 2-D simulation we have studied the electrical performance of V-BCPT in terms of its current gain, cut-off frequency and  $BV_{CEO} \cdot f_T$  product. We have shown that the proposed device is immune to current crowding effect at the edges of the emitter at high collector current densities.

Although poly-Si TFTs are extensively used in several applications such as active matrix displays and memories, research on poly-Si BJTs is very limited. This is due to the low current gain of poly-Si BJTs. This work demonstrates the possibility of realizing a doping-less poly-Si bipolar charge plasma transistor with a high current gain and cut-off frequency. The effect of the grain boundary position on the electrical characteristics of the poly-Si BCPT is also discussed.

In this thesis, a number of doping-less bipolar transistor structures are proposed and investigated. Simulation results show that the doping-less bipolar transistor exhibits a high current gain along with a high  $BV_{CEO} \cdot f_T$  product. Our work demonstrates the possibility of realizing not only bipolar transistors but other field effect transistors using low thermal budget fabrication processes. This may enable the realization of electronic circuits on inexpensive non-silicon substrates such as glass and plastic.

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